PTO/SB/08A (08-03)

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Substitute for form 1449/PTO

Sheet 1

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

of 5

Γ	Complete if Known					
7	Application Number	10/669,141				
ſī	Filing Date	September 23, 2003				
П	First Named Inventor	Milan Kokta				
7	Art Unit	1775				
П	Examiner Name	Stephen J. Stein				
7	Attorney Docket Number	1035-BI4282				

			U. S. PATENT	DOCUMENTS	-
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ^{2 (f known)}	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
227	AA	US- 3,625,868	12/07/1971	Grabmaier et al.	
772	AB	^{US-} 3,736,158	05/29/1973	Cullen et al.	
<i>5</i> 35	AC	US- 3,816,906	06/18/1974	Falckenberg	
3 35	AD	^{US-} 3,883,313	05/13/1975	Cullen et al.	
535	AE	^{US-} 3,885,978	05/27/1975	Doi et al.	
275	AF	^{US-} 3,990,902	11/09/1976	Nishizawa, et al.	
555	AG	US- 3,950,504	04/13/1976	Belding et al.	
535	AH	US- 4,370,739	01/25/1983	Wang et al.	
SSS	Al	^{US-} 4,755,314	07/05/1988	Sakaguchi et al.	-
535	AJ	US- 5,138,298	08/11/1992	Shino	
223	AK	^{US-} 5,850,410	12/15/1998	Kuramata	
533	AL	^{US-} 6,533,874 B1	03/18/2003	Vaudo et al.	
Sas	AM	US- 2003/0188678 A1	10/09/2003	Kokta et al.	
535	AN	US- 6,839,362 B2	01/05/2005	Kokta et al.	
553	AO	US- 6,844,084 B2	01/18/2005	Kokta et al.	
533	AP	US- 3,424,955	01/28/1969	Seiter et al.	
<u>575</u>	AQ	US- 5,557,624	09/17/1996	Stultz, et al.	
222	AR	^{US-} 6,366,596	04/02/2002	Yin, et al.	
222	AS	US- 6,023,479	02/08/2000	Thony, et al.	

			IGN PATENT DOC	UMENTS		
Examiner Initiats*	Cite No.1	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages	Γ
		Country Code ³ Number ⁴ Kind Code ⁸ (if known)	MM-DD-YYYY		Or Relevant Figures Appear	T⁰
202		FR 1,471,976	03/24/1966	Siemens Aktiengesellsc.	Corr. 3,424,955	
223	AU	JP 11-157997	06/15/1999	Kyocera Corporation	Abstract Only ·	
<u> 227</u>	AV	JP 09-278595	10/28/1997	Sumitomo Elect. Ind. Ltd.	Abstract Only	
222	AW	JP 62-188325	08/17/1987	Sumitomo Elect. Ind. Ltd.	Abstract Only	
225	AX	JP 58-211736	12/09/1983	Toshiba Corporation	Abstract Only	
222	AY	JP 07-307316	11/21/1995	Sumitomo Elect. Ind. Ltd.	Abstract Only	

Examiner

Examiner Signature

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Complete if Known		
		Application Number	10/669,141
INFORMATION DISCLOSURE		Filing Date	September 23, 2003
		First Named Inventor	Milan R. Kokta
		Art Unit	1775
(Use	as many sheets as necessary)	Examiner Name	Stephen J. Stein
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			U. S. PATEN	T DOCUMENTS	
Examiner Initials*	Cite No.1	Document Number Number-Kind Code ^{2 (f Innown)}	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
222	ВА	^{US-} 4,963,520	10/16/1990	Yoo, et al.	
535	ВВ	^{US-} 5,982,796	11/09/1999	Kokta, et al.	
SIS	ВС	US- 5,654,973	08/05/1997	Stultz, et al.	
535	BD	US-			
53 8	BE	US-			
	BF	US-			
	BG	US-			
	ВН	US-			
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		FORE	IGN PATENT DOC	JMENTS		
Examiner Initiats*	Cite No.1	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines,	Γ
		Country Code ³ Number ⁴ Kind Code ⁵ (if known)	MM-DD-YYYY	Applicant or Cited Document	Where Relevant Passages Or Relevant Figures Appear	₽ª
335	BT	EP 0 263 171 B1	11/25/1992	UOP		
525	BU	EP 0 762 930 B1	07/12/2000	BP Amoco Corporation		
1/	BV	WO 01/99155 A2	12/27/2001	Nichia Corporation		
<u> </u>	BW	WO 02/095887 A2	11/28/2002	SG Ceramics & Plastics, Inc.		
	BX					
	BY					

Examiner Signature	Start	Sten	Date Considered	5/26/2005

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ĺ				Application Number	10/669,141
INF	ORMATION	DIS	CLOSURE	Filing Date	September 23, 2003
STATEMENT BY APPLICANT				First Named Inventor	Milan R. Kokta
	(Use as many she	ete se n	ecessari	Art Unit	1775
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Sheet	3	of	5	Attorney Docket Number	1035-BI4282

		NON DATENT LITEDATUDE DOCUMENTO	
Examiner Initials*	Cite No.1	NON PATENT LITERATURE DOCUMENTS Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
222	CA	Efimov, A.N., et al., "On an Unusual Azimuthal Orientation Relationship in the System Gallium Nitride Layer on Spinel Substrate", CRYSTALLOGRAPHY REPORTS, 45(2): 312-317 (2000).	
SIS	СВ	Sun C.J., et al., "Mg-doped green light emitting diodes over cubic (1 1 1) MgAl2O4 substrate", APP. PHYS. LETT. 72(19): 2361-2363 (1998).	
277	СС	Efimov, A.N., et al., "Symmetry constraints and epitaxial growth on non-isomorphic substrate", THIN SOLID FILMS 260: 111-117 (1995).	
222	CD	George, T., et al., "Novel symmetry in the growht of gallim nitride on magnesium aluminate substrates", APPL. PHYS. LETT. 68(3): 337-339 (1996).	
SJS	CE	Sun C.J., et al., "Deposition of high quality wurtzite GaN films over cubic (1 1 1) MgAl2O4 substrates using low pressure and metalorganic chemical vapor deposition, " APPL. PHYS. LETT. 68(8): 1129-1131 (1996).	
S35	CF	Nakamura, S., et al., "Characteristics of InGaN multi-quantum-well-structure laser diodes, " APPL. PHYS. LETT. 68(23): 3269-3271 (1996).	
272	CG	Khan, M.A., et al., "Cleaved cavity optically pumped InGaN-GaN laser grown on spinel substrates," APPL. PHYS. LETT. 69(16): 2418-2420 (1996).	
227	СН	Tempel, A., et al., "Nachweis von Stapelfehlern in GaN-Exitaxieschichten mittels Elecktronenbeugung," KRISTALL UND TECHNIK 10(7): 741-746 (1975).	
227	CI	Tempel, A., et al., "Zur Epitaxie von Galliumnitride auf nichtstoechiometrischem Spinell im System GaC1/NH3/He, " KRISTALL UND TECHNICK 10(7): 747-758 (1975)	
272	CJ	K.V. Yumashev, "Saturable absorber Co2+: MgAl2O3 crystal for Q switching of 1.34-um Nd3+: YAIO3 and 1.54-um Er3+: glass lasers," APPLIED OPTICS 38(30): 6343-6346 (1999).	

Examiner Signature	Steel	Ste.	Date Considered	5/	26	/2005	
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			CLOSURE	Filing Date	September 23, 2003	
STATEMENT BY APPLICANT			PPLICANT	First Named Inventor	Milan Kokta	
	(Use as many she	ets as n	ecessary)	Art Unit	1775	
				Examiner Name	Stephen J. Stein	
Sheet	4	of	5	Attorney Docket Number	1035-BI4282	

		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
227	DA	Giess et al., "Growth of Single Crystal MgGa2O4 Spinel", IBM TECHNICAL DISCLOSURE BULLETIN, Vol. 15, no. 1, June 1972, pgs 151-152, XP-002315746.	
222	DB	Anon., "Spinel Crystals for Electronic Devices", MANUFACTURING TECHNOLOGY NOTE, Vol. NTN-77, no. 0735, April 1977, XP-002315747.	-
222	DC	Grabmaier et al., "Czochralski Growth of Magnesium-Aluminum Spinel", J. AMERICAN CERAMIC SOCIETY, Vol. 51, no. 6, June 1968, pgs 355-356, XP-002315185.	
883	DD	Wyon et al., "Czochralski Growth and Optical Properties of Magnesium-Aluminum Spinel Doped with Nickel", JOURNAL OF CRYSTAL GROWHT, NORTH-HOLLAND PUBLISHING CO. AMSTERDAM, NL, Vol. 79, no. 1-3, part 2, 1986, pgs 710-713, XP-002250057.	
272	DE	Pinckney, L.R., "Transparent, high strai point spinel glass-ceramics", JOURNAL OF NON-CRYSTALLINE SOLIDS, Vol. 255, pp. 171-177, 1999.	
217	DF	Nakamura, S. "Current Status and Furture Prospects of InGaN-Based Laser Diodes", ISAP INTERNATIONAL, Vol. 1, pgs. 5-17, 2000.	
حدح	DG	Kisailus D., et al., "Growth of Epitaxial GaN of LiGaO2 Substrates Via a Reaction With Ammonia", J. MATER. RES., Vol. 16, no. 7, pgs 2077-2081, 2001.	
222	DH	Nakamura, S., et al., "InGaN MQW LDs Grown on MgAl2O4 Substrates," In THE BLUE LASER DIODE, (NY: Springer-Verlag), pp. 233-243, 1997 (update included).	
835	DI	Mordoc, H., et al., "Large-band-gap SiC, III-V nitride, and II-vi ZnSe-based Semiconductor Device Technologies", J. APPL. PHYS., Vol. 76, no. 3, pgs 1363-1398, 1994.	
SzS	DJ	Yumashev, K.V., et al., "Nonlinear spectroscopy and passive Q-switching operation of a Co2+: LaMgAl11O19 crystal," J. OPT. SOC. AM. B., 16(12): 2189-2194 (1999).	

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STS	EA	Camargo, M.B., et al., "Co2+ Y3Sc2Ga3O12 (YSGG) Passive Q-Switch for Infared Erbium Lasers," submitted to LEOS in 1994.	
255	EB	Mikhailov, V.P., et al., "Passive Q-switch performance at 1.3u (1.5u) and nonlinear spectroscopy of Co2+: MgAl2O4 and Co2+: LaMgAl11O9 cyrstals," OSA TOPS VOL. 26 Advanced Solid-State Lasers, pp. 317-324 (1999).	
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222	ED	Bimbaum, M., et al., " Co2+: ZnSe Saturable Absorber Q-Switch for the 1.54 Um Er3+: Yb3+: Glass Laser, " OSA TOPS Vol. 10 Advanced Solid State Lasers, pp. 148-151 (1997).	
222	EE	Machida, H., et al., "difficulties encoutered during the Czochralxki growth of TiO2 single crystals," JOURNAL OF CYRSTAL GROWTH, 112: 835-837 (1997).	
222	EF	Camargo, M.B., et al., "Broad-band 1.54 um Saturable Absorber Q-switch with Co2+, " submitted to ASSL in 1995.	
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	EJ		

Examiner		14	Date	~/ /
Signature	Stead	shin.	Considered	5/26/2005

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